

Vishay Siliconix

16 Ω , Low Parasitic Capacitance and Leakage, +12 V / +5 V / +3 V / ± 5 V Quad SPST Switches

DESCRIPTION

The DG411LE, DG412LE, and DG413LE are monolithic quad single-pole-single-throw analog switches. The DG411LE and DG412LE differ only in that they respond to opposite logic levels. The DG413LE has two normally open and two normally closed switches. It can be given various configurations, including four SPST, two SPDT, and one DPDT.

The DG411LE, DG412LE, and DG413LE offer low on resistance of 16 Ω , low parasitic capacitance of 15 pF switch on capacitance, and low charge injection over the signal swing range.

The DG411LE, DG412LE, and DG413LE operate on single and dual supplies. Single supply voltage ranges from 3 V to 16 V while dual supply operation is recommended with \pm 3 V to \pm 8 V. Each switch conducts equally well in both direction when on, and blocks input voltages up to the supply levels when off.

The DG411LE, DG412LE, and DG413LE are available in 16 lead TSSOP, SOIC, and PDIP packages.

FEATURES

 3 V to 16 V single supply or ± 3 V to ± 8 V dual supply



• On-resistance $R_{DS(on)}$: 16 Ω

- Low parasitic capacitance:
 C_{D(on)}: 15 pF, C_{S(off)}: 5 pF
- Less than 8 pC charge injection over the full signal swing range
- Fast switching ton: 16 ns, toff: 9 ns
- TTL, CMOS compatible
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Note

This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

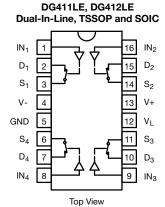
BENEFITS

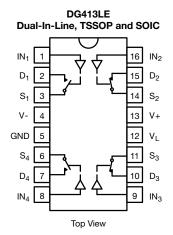
- Wide operation voltage range
- · Low signal errors and distortion
- Fast switching time
- Minimized switching glitch

APPLICATIONS

- Automatic test equipment
- Data acquisition systems
- · Meters and instruments
- Medical and healthcare systems
- Communication systems
- Audio and video signal routing
- Relay replacement
- · Battery powered systems
- Computer peripherals
- Audio and video signal routing

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION







DG411LE, DG412LE, DG413LE

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TRUTH TABLE							
LOGIC	DG411LE	DG412LE					
0	On	Off					
1	Off	On					

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

TRUTH TABLE						
LOGIC	SW ₁ , SW ₄	SW ₂ , SW ₃				
0	Off	On				
1	On	Off				

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

ORDERING INF	ORMATION			
TEMP. RANGE	CONFIGURATION	PACKAGE	PART NUMBER	MIN. ORDER / PACK. QUANTITY
		16-pin TSSOP	DG411LEDQ-GE3	Tube 360 units
		10-рін 1330Р	DG411LEDQ-T1-GE3	Tape and reel, 3000 units
	DG411LE	16-pin SOIC	DG411LEDY-GE3	Tube 500 units
		10-ріп 3010	DG411LEDY-T1-GE3	Tape and reel, 2500 units
		16-pin PDIP	DG411LEDJ-GE3	Tube 500 units
		16-pin TSSOP	DG412LEDQ-GE3	Tube 360 units
40.00		10-ріп 1330ғ	DG412LEDQ-T1-GE3	Tape and reel, 3000 units
-40 °C to +85 °C lead (Pb)-free	DG412LE	10 -:- 0010	DG412LEDY-GE3	Tube 500 units
1000 (1 5) 1100		16-pin SOIC	DG412LEDY-T1-GE3	Tape and reel, 2500 units
		16-pin PDIP	DG412LEDJ-GE3	Tube 500 units
		16 pin TOOOD	DG413LEDQ-GE3	Tube 360 units
		16-pin TSSOP	DG413LEDQ-T1-GE3	Tape and reel, 3000 units
	DG413LE	16-pin SOIC	DG413LEDY-GE3	Tube 500 units
		10-рін 3010	DG413LEDY-T1-GE3	Tape and reel, 2500 units
	-	16-pin PDIP	DG413LEDJ-GE3	Tube 500 units

PARAMETER		LIMIT	UNIT	
V+ to V-		-0.3 to +18		
GND to V-		18		
V _L		(GND -0.3) to (V+) +0.3	V	
I _N a, V _S , V _D		-0.3 to (V+) +0.3 or 30 mA, whichever occurs first		
Continuous current (any terminal)		30	A	
Peak current, S or D (pulsed 1 ms, 10 % de	uty cycle)	100	mA	
Storage temperature	(DQ, DY suffix)	-65 to +125	°C	
Storage temperature	(AK suffix)	-65 to +150	1	
	16-pin TSSOP °	450		
Power dissipation (packages) b	16-pin SOIC ^d	650	mW	
	16-pin CerDIP ^e	900	7	
ESD human body model (HBM); per ANSI	2500	V		
Latch up current, per JESD78D	400	mA		

Notes

- a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings
- b. All leads welded or soldered to PC board
- c. Derate 7 mW/°C above 75 °C
- d. Derate 7.6 mW/°C above 75 °C
- e. Derate 12 mW/°C above 75 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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SPECIFICATIONS a (Single Su	pply 12 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. b	TYP. °	A SUFFIX LIMITS -55 °C to +125 °C		D SUFFIX LIMITS -40 °C to +85 °C		UNIT
		V+ = 12 V, V- = 0 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^f$			MIN. d	MAX. d	MIN. d	MAX.d	
Analog Switch	•								
Analog signal range e	V _{ANALOG}		Full	-	0	12	0	12	V
Drain-source on-resistance	R _{DS(on)}	V+ = 10.8 V, V- = 0 V	Room	16	-	26	-	26	Ω
	DO(OII)	$I_S = 10 \text{ mA}, V_D = 2/9 \text{ V}$	Full	-	-	40	-	35	
	I _{S(off)}		Room	-	-1	1	-1	1	
Switch off leakage current	-3(011)	$V_D = 1/11 \text{ V}, V_S = 11/1 \text{ V}$	Full	-	-15	15	-10	10	
owner on roundge ourrone	I _{D(off)}	v ₀ = 1, 1, v ₃ = 1, 1, v	Room	-	-1	1	-1	1	nA
	'D(off)		Full	-	-15	15	-10	10	11/1
Channel on leakage current	l ₌ ,	$V_S = V_D = 11/1 V$	Room	-	-1	1	-1	1	
Chamilei on leakage current	I _{D(on)}		Full	-	-15	15	-10	10	
Digital Control									
Input current, VIN Low	I _{IL}	V _{IN} under test = 0.8 V	Full	0.01	-1.5	1.5	-1	1	
Input current, VIN High	I _{IH}	V _{IN} under test = 2.4 V	Full		-1.5	1.5	-1	1	μΑ
Dynamic Characteristics				•					
-			Room	16	-	50	-	50	ns
Turn-on time	t _{ON}	$R_1 = 300 \Omega, C_1 = 35 pF,$	Full	-	-	70	-	60	
-		$V_S = 5 \text{ V}$, see figure 2	Room	9	-	30	-	30	
Turn-off time	t _{OFF}		Full	-	-	48	-	40	
Break-before-make time delay	t _D	DG413L only, $V_S = 5 \text{ V}$, $R_L = 300 \Omega$, $CL = 35 \text{ pF}$	Room	5	-	-	-	-	
Charge injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	6.6	1	ı	-	-	рC
Off-isolation e	OIRR	-	Room	68.4	1	ı	-	-	
Channel-to-channel crosstalk ^e	X _{TALK}	$R_L = 50~\Omega,~C_L = 5~pF,~f = 1~MHz$	Room	114	-	-	-	-	dB
Source off capacitance e	C _{S(off)}		Room	5	-	-	-	-	
Drain off capacitance e	C _{D(off)}	f = 1 MHz	Room	6	-	-	-	-	рF
Channel-on capacitance e	C _{D(on)}		Room	15	-	-	-	-	
Power Supplies	. ,								
Death and the			Room	0.02	-	1	-	1	
Positive supply current	l+		Full	-	-	7.5	-	5	1
Negative supply current			Room	-0.002	-1	-	-1	-	
	I-		Full	-	-7.5	-	-5	-	
Logio guante sumant		$V_{IN} = 0 \text{ V or 5 V}$	Room	0.002	-	1	-	1	μA
Logic supply current	IL		Full	-	-	7.5	-	5	
Ground current	lovo			-0.002	-1	=	-1	-	
around current	I _{GND}		Full	-	-7.5	ı	-5	-	

- a. Refer to PROCESS OPTION FLOWCHART
- b. Room = 25 °C, full = as determined by the operating temperature suffix
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- e. Guaranteed by design, not subject to production test
- f. V_{IN} = input voltage to perform proper function
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test



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SPECIFICATIONS a (Dual Supp	ly ± 5 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.b	TYP. °	A SUFFIX LIMITS -55 °C to +125 °C		LIN	JFFIX IITS o +85 °C	UNIT
		$V_{+} = 5 V, V_{-} = -5 V$ $V_{L} = 5 V, V_{IN} = 2.4 V, 0.8 V^{f}$			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch			l	l .		I.	ı		L
Analog signal range e	V _{ANALOG}		Full	-	-5	5	-5	5	V
Drain course on reciptores	Р	V+ = 5 V, V- = -5 V,	Room	18	-	30		30	Ω
Drain-source on-resistance	R _{DS(on)}	$I_S = 10 \text{ mA}, V_D = \pm 3.5 \text{ V}$	Full	-	1	42	-	37	52
	مر بما		Room	-	-1	1	-1	1	
Switch off leakage current ^g	I _{S(off)}	V+ = 5.5, V- = -5.5 V,	Full	-	-15	15	-10	10	
Switch on leakage current 9	l	$V_D = \pm 4.5 \text{ V}, V_S = \pm 4.5 \text{ V}$	Room	-	-1	1	-1	1	nA
	I _{D(off)}		Full	-	-15	15	-10	10	II/A
Channel on leakage current ^g	1	V+ = 5.5 V, V- = -5.5 V,	Room	-	-1	1	-1	1	
Charmer of reakage current 9	I _{D(on)}	$V_S = V_D = \pm 4.5 \text{ V}$	Full	-	-15	15	-10	10	
Digital Control									
Input current, V _{IN} low ^e	$I_{\rm IL}$	V _{IN} under test = 0.8 V	Full	0.05	-1.5	1.5	-1	1	μA
Input current, V _{IN} high ^e	I _{IH}	V_{IN} under test = 2.4 V	Full	0.05	-1.5	1.5	-1	1	μΛ
Dynamic Characteristics									
Turn-on time e	t _{ON}		Room	17	-	50	-	50	ns
rum-on time °	ON	$R_L = 300 \Omega$, $C_L = 35 pF$,	Full	-	-	70	-	60	
Turn-off time e	toff	$V_S = \pm 3.5 \text{ V}$, see figure 2	Room	12	-	35	-	35	
rum-on time	·OFF		Full	-	ı	50	-	40	
Break-before-make time delay ^e	t_D	DG413L only, $V_S = 3.5 \text{ V}$, $R_L = 300 \Omega$, $C_L = 35 \text{ pF}$	Room	5	-	-	-	-	
Charge injection ^e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	5.8	-	-	-	-	рС
Off isolation e	OIRR		Room	68	-	-	-	-	
Channel-to-channel crosstalk ^e	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	113	-	-	-	-	dB
Source off capacitance e	C _{S(off)}		Room	5	-	-	-	-	
Drain off capacitance e	C _{D(off)}	f = 1 MHz	Room	6	-	-	-	-	рF
Channel on capacitance e	C _{D(on)}		Room	14	1	-	-	-	
Power Supplies									
Positive supply current e	l+		Room	0.03	ı	1	-	1	
1 ositive supply current *	I+ 		Full	-	-	7.5	-	5]
Negative supply current ^e	 -		Room	-0.002	-1	-	-1	-	
rvegative supply current		V 0 V or 5 V	Full	-	-7.5	-	-5	-	,.,
Logio supply ourrent 6	I.	$V_{IN} = 0 \text{ V or 5 V}$	Room	0.002		1		1	μA
Logic supply current e	ΙL		Full	-	=	7.5	-	5	
Ground current e	1		Room	-0.002	-1	-	-1	-	
Ground current *	I _{GND}		Full	-	-7.5	-	-5	-	

- a. Refer to PROCESS OPTION FLOWCHART
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- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test



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SPECIFICATIONS a (S	SPECIFICATIONS ^a (Single Supply 5 V)									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 5 V, V- = 0 V	TEMP.b	TEMP.b	TYP. °	LIN -55 °C	IFFIX IITS to +125 C	LIM	IFFIX IITS D +85 °C	UNIT
		$V_L = 5 \text{ V}, V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{f}$			MIN. d	MAX. d	MIN. d	MAX. d		
Analog Switch										
Analog signal range ^e	V _{ANALOG}		Full	-	-	5	-	5	V	
Drain-source on-resistance e	B _{na} ,	V+ = 4.5 V,	Room	36	-	50	-	50	Ω	
Dialii-Source off-resistance	R _{DS(on)}	$I_S = 5 \text{ mA}, V_D = 1 \text{ V}, 3.5 \text{ V}$	Full	-	-	88	-	75	22	
Dynamic Characteristics										
Turn-on time e	+		Room	27	1	50	-	50	ns	
rum-on time •	t _{ON}	$R_L = 300 \Omega, C_L = 35 pF,$	Hot	-	-	90	-	60		
Turn-off time e	t _{OFF}	$V_S = 3.5 V$, see figure 2	Room	15	-	30	-	30		
Turn-on time s			Hot	-	-	55	-	40	110	
Break-before-make time delay ^e	t _D	DG413L only, $V_S = 3.5 \text{ V}$, $R_L = 300 \Omega$, $C_L = 35 \text{ pF}$	Room	11	-	-	-	-		
Charge injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	3.3	-	-	-	-	рC	
Power Supplies										
Positive supply current e	I+		Room	0.02	-	1	-	1		
Fositive supply current	1+		Hot	-	-	7.5	-	5		
Negative aupply current 6	l-		Room	-0.002	-1	-	-1	-		
Negative supply current e	-	V _{IN} = 0 V or 5 V	Hot	-	-7.5	-	-5	-		
Logio cupply current 6		VIN = O V OL 2 V	Room	0.002	-	1	-	1	μΑ	
Logic supply current e	IL		Hot	-	-	7.5	-	5		
Ground current e	1		Room	-0.002	-1	-	-1	-		
Ground current -	I _{GND}		Hot	-	-7.5	-	-5	-		

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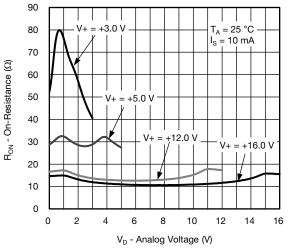
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SPECIFICATIONS a (S	Single Sup	ply 3 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. b	TYP. °	-55 °C	X LIMITS to +125 C	LIM	IFFIX IITS o +85 °C	UNIT
		$V_{L} = 3 V, V_{-} = 0 V$ $V_{L} = 3 V, V_{IN} = 0.4 V, 2.0 V^{f}$			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch									
Analog signal range e	V _{ANALOG}		Full	-	0	3	0	3	V
Drain-source on-resistance	R _{DS(on)}	V+ = 3.0 V, V- = 0 V,	Room	71	52	90	52	90	Ω
	03(011)	$I_S = 5 \text{ mA}, V_D = 0.5, 2.2 \text{ V}$	Full	-	-	110	-	102	
	مريما		Room	-	-1	1	-1	1	
Switch off leakage current ^g	I _{S(off)}	V+ = 3.3, V- = 0 V,	Full	-	-15	15	-10	10	
Switch on leakage current	I _{D(off)}	$V_D = 1, 2 V, V_S = 2, 1 V$	Room	-	-1	1	-1	1	nA
			Full	-	-15	15	-10	10	IIA
Ohamadan laalaan aat 0	I _{D(on)}	V+ = 3.3 V, V- = 0 V,	Room	-	-1	1	-1	1	-
Channel on leakage current ⁹		$V_S = V_D = 1, 2 V$	Full	-	-15	15	-10	10	
Digital Control									
Input current, V _{IN} low	I _{IL}	V _{IN} under test = 0.4 V	Full	0.005	-1.5	1.5	-1	1	μΑ
Input current, V _{IN} high	I _{IH}	V _{IN} under test = 2.4 V	Full	0.005	-1.5	1.5	-1	1	
Dynamic Characteristics									
T			Room	57	-	85	-	85	
Turn-on time	t _{ON}	$R_L = 300 \Omega, C_L = 35 pF,$	Full	-	-	150	-	110	
T##:		$V_S = 1.5 \text{ V}$, see figure 2	Room	25	-	60	-	60	ns
Turn-off time	t _{OFF}		Full	-	-	100	-	85	113
Break-before-make time delay	t _D	DG413L only, $V_S = 1.5 \text{ V}$, $R_L = 300 \Omega$, $C_L = 35 \text{ pF}$	Room	24	-	-	-	-	
Charge injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	2	-	-	-	-	рС
Off isolation e	OIRR		Room	68	-	-	-	-	
Channel-to-channel crosstalk e	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	107	-	-	-	-	dB
Source off capacitance e	C _{S(off)}		Room	6	-	-	-	-	
Drain off capacitance e	C _{D(off)}	f = 1 MHz	Room	7	-	-	-	-	pF
Channel on capacitance e	C _{D(on)}		Room	15	-	-	-	-	

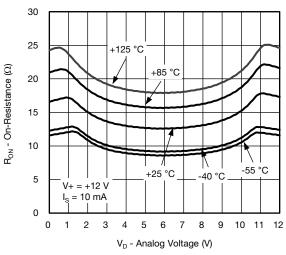
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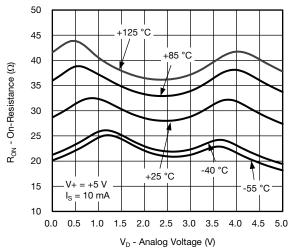
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



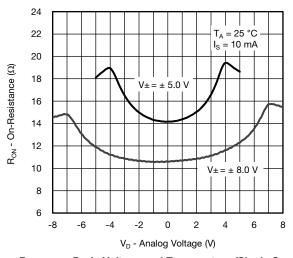
R_{DS(on)} vs. Drain Voltage (Single Supply)



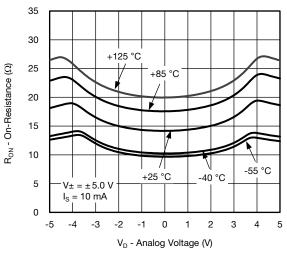
R_{DS(on)} vs. Drain Voltage and Temperature



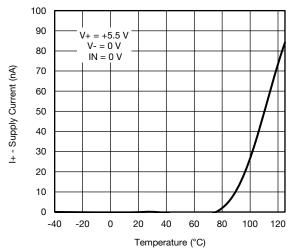
R_{DS(on)} vs. Drain Voltage and Temperature



R_{DS(on)} vs. Drain Voltage and Temperature (Single Supply)



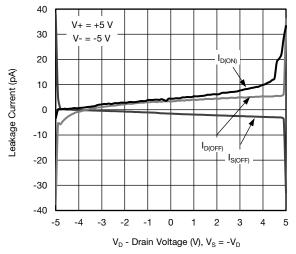
Supply Current vs. Temperature



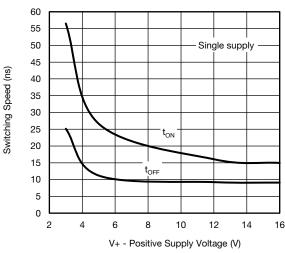
Switching Time vs. Single Supply

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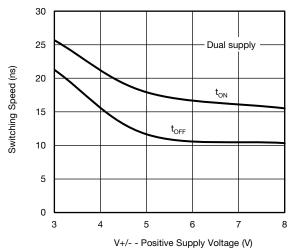
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



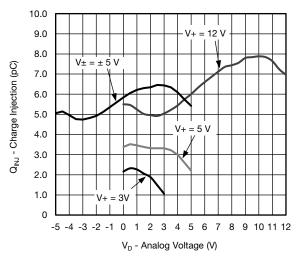
Leakage Current vs. Drain Voltage



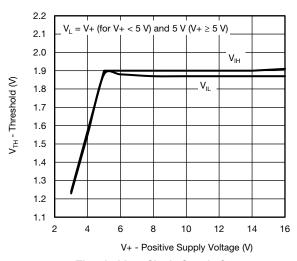
Switching Time vs. Single Supply Voltage



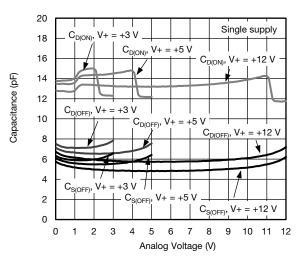
Switching Time vs. Dual Supply Voltage



Charge Injection vs. Drain Voltage



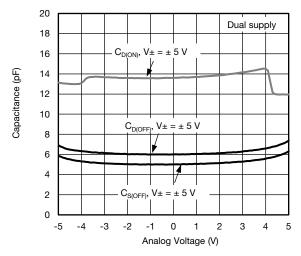
Threshold vs. Single Supply Current



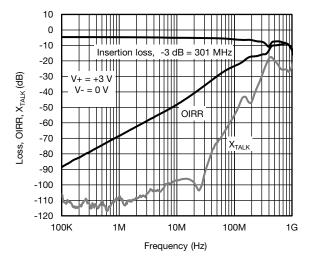
Drain Capacitance vs. Drain Voltage (Single Supply)

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

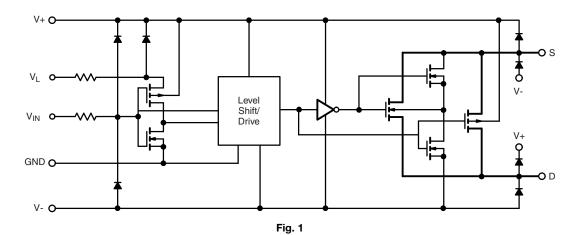






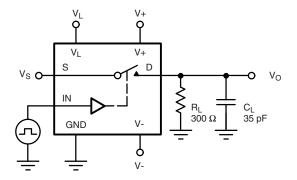
Insertion Loss, Off Isolation and Crosstalk vs. Frequency

SCHEMATIC DIAGRAM (Typical Channel)



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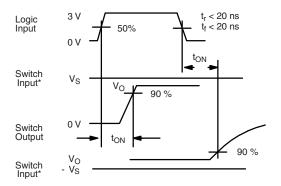
TEST CIRCUITS



 $\ensuremath{\text{C}_{\text{L}}}$ (includes fixture and stray capacitance)

$$V_O = V_S$$

$$\frac{R_L}{R_L + r_{DS(on)}}$$



Note: Logic input waveform is inverted for switches that have the opposite logic sense control

Fig. 2 - Switching Time

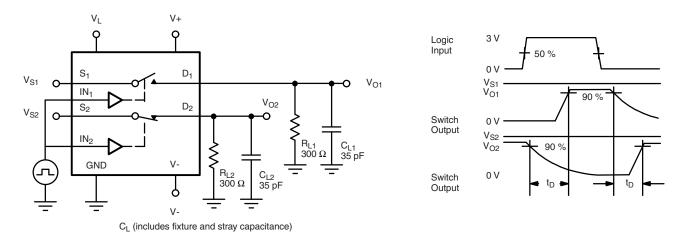
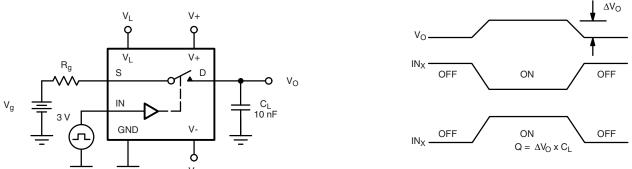


Fig. 3 - Break-Before-Make (DG413LE)



 $\ensuremath{\mathsf{IN}_X}$ dependent on switch configuration Input polarity determined by sense of switch.

Fig. 4 - Charge Injection

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TEST CIRCUITS

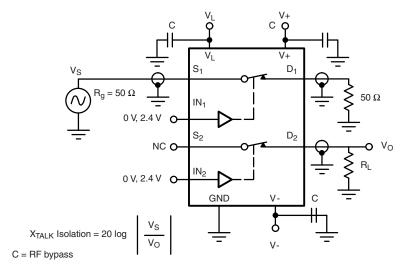


Fig. 5 - Crosstalk

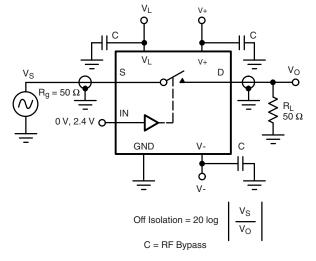


Fig. 6 - Off-Isolation

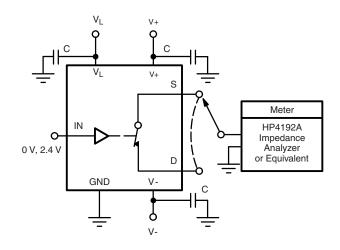


Fig. 7 - Source / Drain Capacitances



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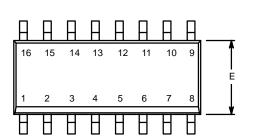
PRODUC	T SUMMA	RY							
Part	DG411LE	DG411LE	DG411LE	DG412LE	DG412LE	DG412LE	DG413LE	DG413LE	DG413LE
number Status code	2	2	2	2	2	2	2	2	2
Configuration	SPST x 4,	SPST x 4,							
Single supply min. (V)	3	3	3	3	3	3	3	3	3
Single supply max. (V)	16	16	16	16	16	16	16	16	16
Dual supply min. (V)	3	3	3	3	3	3	3	3	3
Dual supply max. (V)	8	8	8	8	8	8	8	8	8
On-resistan ce (Ω)	16	16	16	16	16	16	16	16	16
Charge injection (pC)	6.6	6.6	6.6	6.6	6.6	6.6	6.6	6.6	6.6
Source on capacitance (pF)	15	15	15	15	15	15	15	15	15
Source off capacitance (pF)	5	5	5	5	5	5	5	5	5
Leakage switch on typ. (nA)	-	-	-	-	-	-	-	-	-
Leakage switch off max. (nA)	1	1	1	1	1	1	1	1	1
-3 dB bandwidth (MHz)	-	-	-	-	-	-	-	-	-
Package	Plastic DIP-16	SO-16 (narrow) AS	TSSOP-16	TSSOP-16	SO-16 (narrow) AS	Plastic DIP-16	TSSOP-16	Plastic DIP-16	SO-16 (narrow) AS
Functional circuit / applications	Multi purpose, instrumentation, medical and healthcare, portable	Multi purpose, instrumentation medical and healthcare, portable							
Interface	Parallel	Parallel							
Single supply operation	Yes	Yes							
Dual supply operation	Yes	Yes							
Turn on time max. (ns)	50	50	50	50	50	50	50	50	50
Crosstalk and off isolation	-114	-114	-114	-114	-114	-114	-114	-114	-114

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?78091.





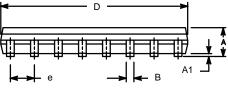
SOIC (NARROW): 16-LEAD JEDEC Part Number: MS-012

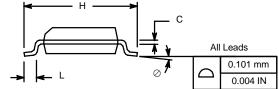


	MILLIM	IETERS	INC	HES			
Dim	Min	Max	Min	Max			
Α	1.35	1.75	0.053	0.069			
A ₁	0.10	0.20	0.004	0.008			
В	0.38	0.51	0.015	0.020			
С	0.18	0.23	0.007	0.009			
D	9.80	10.00	0.385	0.393			
Е	3.80	4.00	0.149	0.157			
е	1.27	BSC	0.050	BSC			
Н	5.80	6.20	0.228	0.244			
L	0.50	0.93	0.020	0.037			
0	0°	8°	0°	8°			
FCN: S-0	FCN: S-03946—Rev. F. 09-Jul-01						

ECN: S-03946—Rev. F, 09-Jul-01

DWG: 5300

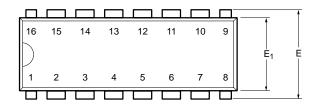


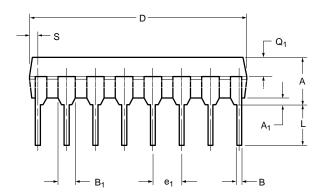


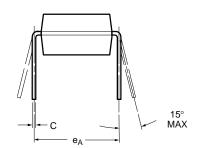
www.vishay.com 02-Jul-01



PDIP: 16-LEAD





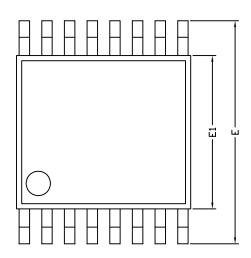


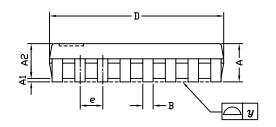
	MILLIN	IETERS	INC	HES		
Dim	Min	Max	Min	Max		
Α	3.81	5.08	0.150	0.200		
A ₁	0.38	1.27	0.015	0.050		
В	0.38	0.51	0.015	0.020		
B ₁	0.89	1.65	0.035	0.065		
С	0.20	0.30	0.008	0.012		
D	18.93	21.33	0.745	0.840		
Е	7.62	8.26	0.300	0.325		
E ₁	5.59	7.11	0.220	0.280		
e ₁	2.29	2.79	0.090	0.110		
e _A	7.37	7.87	0.290	0.310		
L	2.79	3.81	0.110	0.150		
Q ₁	1.27	2.03	0.050	0.080		
S	0.38	1.52	.015	0.060		
ECN: S-03946—Rev. D, 09-Jul-01						

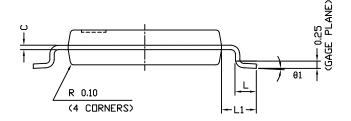
Document Number: 71261 www.vishay.com 06-Jul-01 www.vishay.com



TSSOP: 16-LEAD







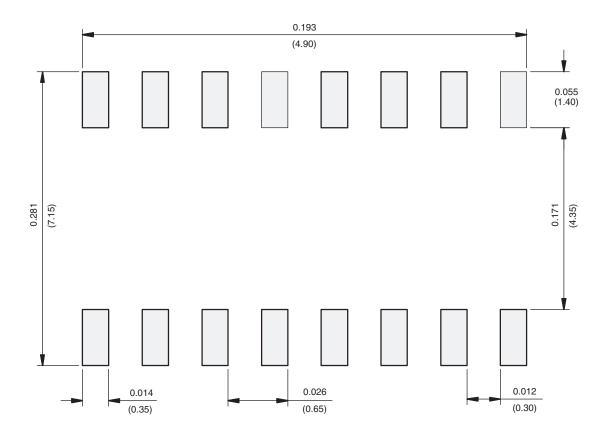
	DII	MENSIONS IN MILLIMETE	RS
Symbols	Min	Nom	Max
А	=	1.10	1.20
A1	0.05	0.10	0.15
A2	=	1.00	1.05
В	0.22	0.28	0.38
С	=	0.127	-
D	4.90	5.00	5.10
E	6.10	6.40	6.70
E1	4.30	4.40	4.50
е	-	0.65	-
L	0.50	0.60	0.70
L1	0.90	1.00	1.10
у	=	-	0.10
θ1	0°	3°	6°
ECN: S-61920-Rev. D. 23-0	Oct-06	<u> </u>	

DWG: 5624

Document Number: 74417 www.vishay.com 23-Oct-06



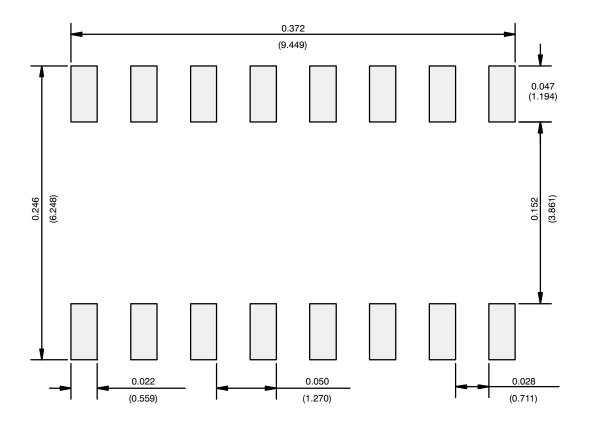
RECOMMENDED MINIMUM PAD FOR TSSOP-16



Recommended Minimum Pads Dimensions in inches (mm)



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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